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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	EBI/EMI, I²C, SCI, SPI, USB OTG
Peripherals	LVD, PWM, WDT
Number of I/O	69
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 12x12b; D/A 1x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	104-LFBGA
Supplier Device Package	104-MAPBGA (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf51je256vml

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2 Pinouts and Pin Assignments

2.1 104-Pin MAPBGA

The following figure shows the 104-pin MAPBGA pinout configuration.

	1	2	3	4	5	6	7	8	9	10	11	
A	PTF6	PTF7	USB_DP	USB_DM	VUSB33	PTF4	PTF3	FB_AD12	PTJ7	PTJ5	PTJ4	A
B	PTG0	PTA0	PTG3	VBUS	PTF5	PTJ6	PTH0	PTE5	PTF0	PTF1	PTF2	B
C	IRO	PTG4	PTA6	PTG2	PTG6	PTG5	PTG7	PTH1	PTE4	PTE6	PTE7	C
D	PTA5	PTA4	PTB1	VDD1		VDD2		VDD3	PTA1	PTE3	PTE2	D
E	VSSA	PTA7	PTB0						PTA2	PTJ3	PTE1	E
F	VREFL			PTG1				PTC7	PTJ2	PTJ0	PTJ1	F
G	ADP2								PTD5	PTD7	PTE0	G
H			PTA3	VSS1		VSS2		VSS3	PTD4	PTD3	PTD2	H
J	ADP0		PTH7	PTH6	PTH4	PTH3	PTH2	PTD6	PTC2	PTC0	PTC1	J
K			ADP1	PTH5	PTB6	PTB7	PTC3	PTD1	PTC4	PTC5	PTC6	K
L	ADP3	DACO		VREFO	VREFH	VDDA	PTB3	PTB2	PTD0	PTB5	PTB4	L
	1	2	3	4	5	6	7	8	9	10	11	

Figure 2. 104-Pin MAPBGA

2.2 100-Pin LQFP

The following figure shows the 100-pin LQFP pinout configuration.

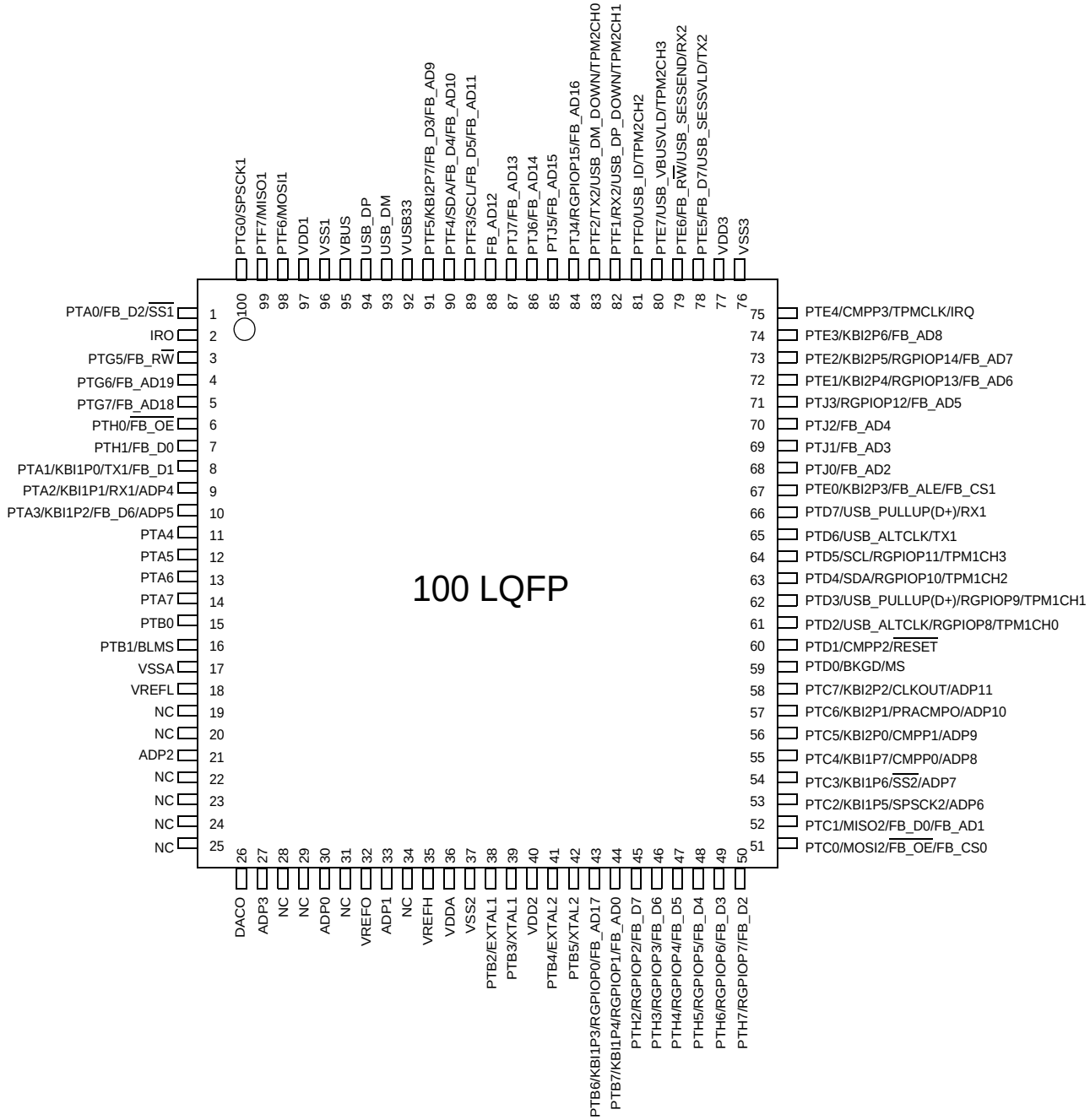


Figure 3. 100-Pin LQFP

2.3 81-Pin MAPBGA

The following figure shows the 81-pin MAPBGA pinout configuration.

	1	2	3	4	5	6	7	8	9	
A	IRO	PTG0	PTF6	USB_DP	VBUS	VUSB33	PTF4	PTF3	PTE4	A
B	PTF7	PTA0	PTG1	USB_DM	PTF5	PTE7	PTF1	PTF0	PTE3	B
C	PTA4	PTA5	PTA6	PTA1	PTF2	PTE6	PTE5	PTE2	PTE1	C
D		PTA7	PTB0	PTB1	PTA2	PTA3	PTD5	PTD7	PTE0	D
E				VDD2	VDD3	VDD1	PTD2	PTD3	PTD6	E
F		ADP2		VSS2	VSS3	VSS1	PTB7	PTC7	PTD4	F
G	ADP0	DACO	ADP3		VREFO	PTB6	PTC0	PTC1	PTC2	G
H			ADP1		PTC3	PTC4	PTD0	PTC5	PTC6	H
J	VSSA	VREFL	VREFH	VDDA	PTB2	PTB3	PTD1	PTB4	PTB5	J
	1	2	3	4	5	6	7	8	9	

Figure 4. 81-Pin MAPBGA

Table 3. Package Pin Assignments (continued)

Package				Default Function	Alternate 1	Alternate 2	Alternate 3	Composite Pin Name
104 MAPBGA	100 LQFP	81 MAPBGA	80 LQFP					
H4	96	F6	76	VSS1	—	—	—	VSS1
D4	97	E6	77	VDD1	—	—	—	VDD1
A1	98	A3	78	PTF6	MOSI1	—	—	PTF6/MOSI1
A2	99	B1	79	PTF7	MISO1	—	—	PTF7/MISO1
B1	100	A2	80	PTG0	SPSCK1	—	—	PTG0/SPSCK1
F4	—	B3	—	PTG1	USB_SESSEND	—	—	PTG1/USB_SESSEND
C4	—	—	—	PTG2	USB_DM_DOWN	—	—	PTG2/USB_DM_DOWN
B3	—	—	—	PTG3	USB_DP_DOWN	—	—	PTG3/USB_DP_DOWN
C2	—	—	—	PTG4	USB_SESSVLD	—	—	PTG4/USB_SESSVLD

3 Preliminary Electrical Characteristics

This section contains electrical specification tables and reference timing diagrams for the MCF51JE256/128 microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

3.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 4. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

3.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in the following table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

Table 5. Absolute Maximum Ratings

#	Rating	Symbol	Value	Unit
1	Supply voltage	V_{DD}	–0.3 to 3.8	V
2	Maximum current into V_{DD}	I_{DD}	120	mA
3	Digital Input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
4	Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
5	Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}).

3.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. In order to take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 6. Thermal Characteristics

#	Symbol	Rating		Value	Unit
1	T_A	Operating temperature range (packaged):			°C
			MCF51JE256	–40 to 105	
			MCF51JE128	–40 to 105	
2	T_{JMAX}	Maximum junction temperature		135	°C
3	θ_{JA}	Thermal resistance[1,2,3,4] Single-layer board — 1s			°C/W
			104-pin MBGA	67	
			100-pin LQFP	53	
			81-pin MBGA	67	
			80-pin LQFP	53	
4	θ_{JA}	Thermal resistance[1, 2, 3, 4] Four-layer board — 2s2p			°C/W
			104-pin MBGA	39	
			100-pin LQFP	41	
			81-pin MBGA	39	
			80-pin LQFP	39	

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2 Junction to Ambient Natural Convection
3 1s — Single layer board, one signal layer
4 2s2p — Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

Table 10. Supply Current Characteristics (continued)

#	Symbol	Parameter	Bus Freq	V_{DD} (V)	Typical[1]	Maximum	Unit	Temperature (°C)	C
6	$S2I_{DD}$	Stop2 mode supply current[4]							
			N/A	3	0.410	1	μA	-40 to 25	P
			N/A	3	3.7	10	μA	70	C
			N/A	3	10	20	μA	85	C
			N/A	3	21	31.5	μA	105	P
			N/A	2	0.410	0.640	μA	-40 to 25	C
			N/A	2	3.4	9	μA	70	C
			N/A	2	9.5	18	μA	85	C
			N/A	2	20	30	μA	105	C
7	$S3I_{DD}$	Stop3 mode supply current No clocks active	N/A	3	0.750	1.3	μA	-40 to 25	P
			N/A	3	8.5	18	μA	70	C
			N/A	3	20	28	μA	85	C
			N/A	3	53	63	μA	105	P
			N/A	2	0.400	0.900	μA	-40 to 25	C
			N/A	2	8.2	16	μA	70	C
			N/A	2	18	26	μA	85	C
			N/A	2	47	59	μA	105	C

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 ON = System Clock Gating Control registers turn on system clock to the corresponding modules.

3 OFF = System Clock Gating Control registers turn off system clock to the corresponding modules.

4 All digital pins must be configured to a known state to prevent floating pins from adding current. Smaller packages may have some pins that are not bonded out; however, software must still be configured to the largest pin package available so that all pins are in a known state. Otherwise, floating pins that are not bonded in the smaller packages may result in a higher current draw. NOTE: I/O pins are configured to output low; input-only pins are configured to pullup-enabled. IRO pin connects to ground. FB_AD12 pin is pullup-enabled. DACO, and VREFO pins are at reset state and unconnected.

Table 11. Stop Mode Adders

#	Parameter	Condition	Temperature (°C)					Units	C
			-40	25	70	85	105		
1	LPO	—	50	75	100	150	250	nA	D
2	EREFSTEN	RANGE = HGO = 0	600	650	750	850	1000	nA	D
3	IREFSTEN[1]	—	—	73	80	93	125	μA	T
4	TOD	Does not include clock source current	50	75	100	150	250	nA	D

Table 11. Stop Mode Adders (continued)

#	Parameter	Condition	Temperature (°C)					Units	C
			-40	25	70	85	105		
5	LVD[1]	LVDSE = 1	116	117	126	132	172	µA	T
6	PRACMP[1]	Not using the bandgap (BGBE = 0)	17	18	24	35	74	µA	T
7	ADC[1]	ADLPC = ADLSMP = 1 Not using the bandgap (BGBE = 0)	75	85	100	115	165	µA	T
8	DAC[1]	High power mode; no load on DACO	500	500	500	500	500	µA	T

1 Not available in stop2 mode.

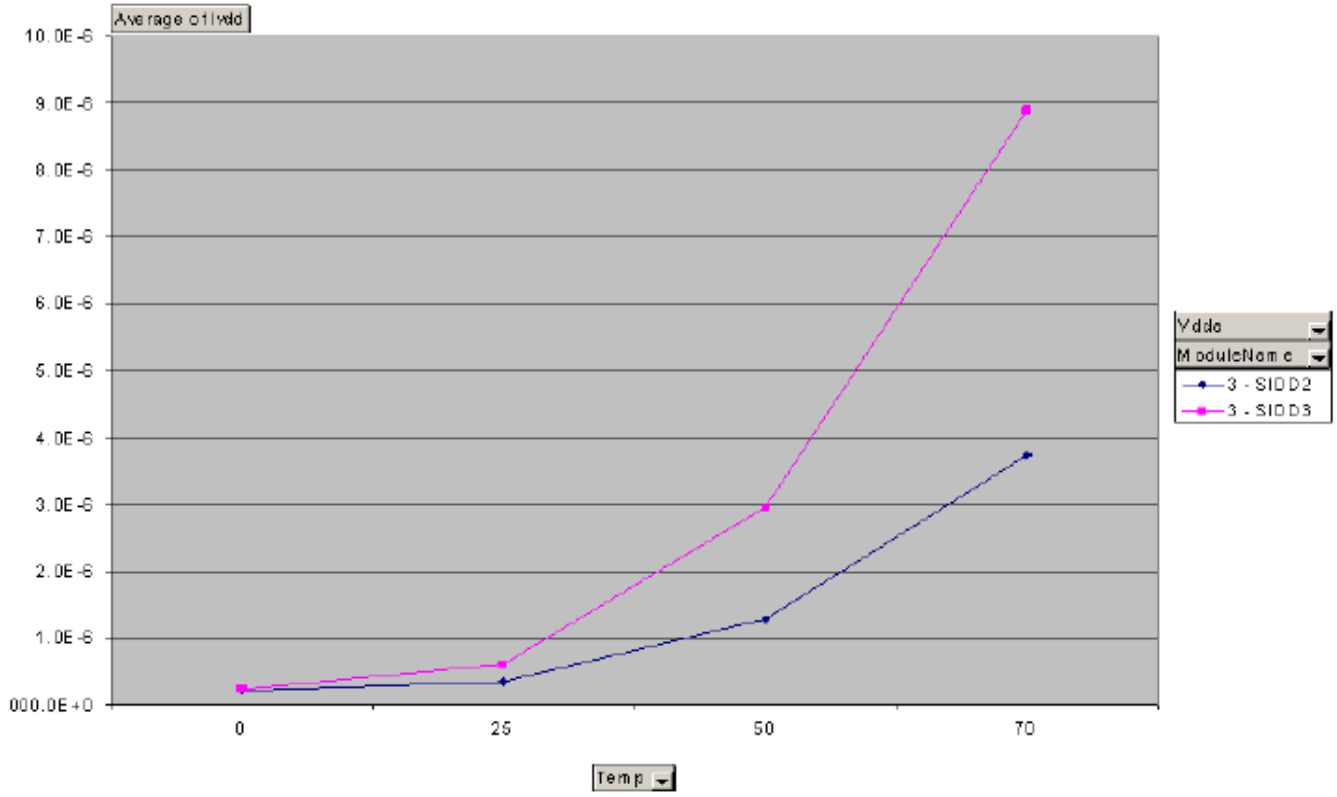


Figure 6. Stop IDD versus Temperature

3.7 PRACMP Electricals

Table 12. PRACMP Electrical Specifications

#	Characteristic	Symbol	Minimum	Typical	Maximum	Unit	C
1	Supply voltage	V_{PWR}	1.8	—	3.6	V	P
2	Supply current (active) (PRG enabled)	I_{DDACT1}	—	—	80	μA	D
3	Supply current (active) (PRG disabled)	I_{DDACT2}	—	—	40	μA	D
4	Supply current (ACMP and PRG all disabled)	I_{DDDIS}	—	—	2	nA	D
5	Analog input voltage	VAIN	V_{SS} – 0.3	—	V_{DD}	V	D
6	Analog input offset voltage	VAIO	—	5	40	mV	D
7	Analog comparator hysteresis	V_H	3.0	—	20.0	mV	D
8	Analog input leakage current	I_{ALKG}	—	—	1	nA	D
9	Analog comparator initialization delay	t_{AINIT}	—	—	1.0	μs	D
10	Programmable reference generator inputs	V_{In2} (V_{DD25})	1.8	—	2.75	V	D
11	Programmable reference generator setup delay	t_{PRGST}	—	1	—	μs	D
12	Programmable reference generator step size	Vstep	0.75	1	1.25	LSB	D
13	Programmable reference generator voltage range	Vprgout	V_{In}/32	—	V_{in}	V	P

3.8 12-bit DAC Electricals

Table 13. DAC 12LV Operating Requirements

#	Characteristic	Symbol	Minimum	Maximum	Unit	C
1	Supply voltage	V_{DDA}	1.8	3.6	V	P
2	Reference voltage	V_{DACR}	1.15	3.6	V	C
3	Temperature	T_A	-40	105	°C	C
4	Output load capacitance[1]	C_L	—	100	pF	C
5	Output load current	I_L	—	1	mA	C

1 A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

Table 14. DAC 12-Bit Operating Behaviors

#	Characteristic	Symbol	Minimum	Typical	Maximum	Unit	C	Notes
15	Temperature drift of offset voltage (DAC set to 0x0800)[1]	T_{co}	—	—	2	mV	T	See Typical Drift figure that follows.
16	Offset aging coefficient	A_C	—	—	8	µV/yr	T	

1 See Typical Drift figure that follows.

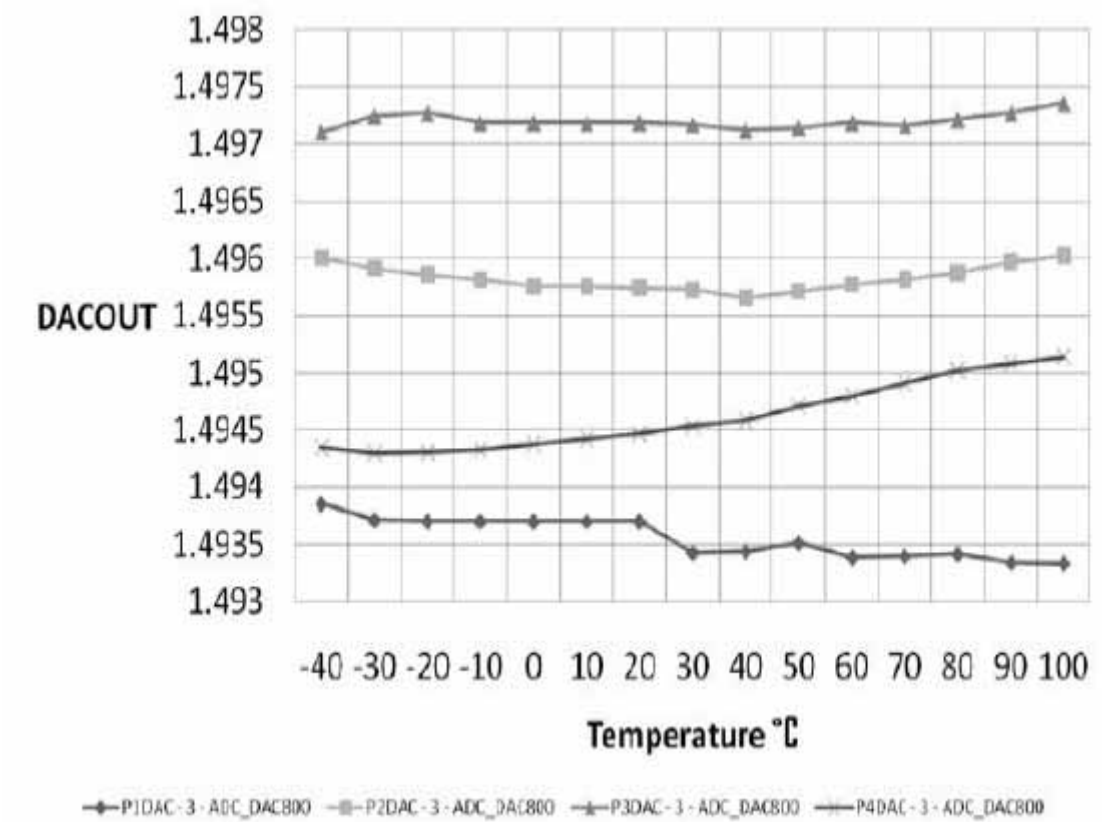


Figure 7. Offset at Half Scale vs Temperature

3.9 ADC Characteristics

Table 15. 12-bit ADC Operating Conditions

#	Symb	Characteristic	Conditions	Minimum	Typical[1]	Maximum	Unit	C
1	V_{DDAD}	Supply voltage	Absolute	1.8	—	3.6	V	D
2	ΔV_{DDAD}	Supply voltage	Delta to V_{DD} (V_{DD}-V_{DDAD})[2]	-100	0	+100	mV	D
3	ΔV_{SSAD}	Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSAD})[2]	-100	0	+100	mV	D
4	V_{REFH}	Ref Voltage High	—	1.13	V_{DDAD}	V_{DDAD}	V	D

Table 15. 12-bit ADC Operating Conditions (continued)

#	Symb	Characteristic	Conditions	Minimum	Typical[1]	Maximum	Unit	C
5	V_{REFL}	Ref Voltage Low	—	V_{SSAD}	V_{SSAD}	V_{SSAD}	V	D
6	V_{ADIN}	Input Voltage	—	V_{REFL}	—	V_{REFH}	V	D
7	C_{ADIN}	Input Capacitance	—	—	4	5	pF	C
8	R_{ADIN}	Input Resistance	—	—	2	5	kΩ	C
9	R_{AS}	Analog Source Resistance[3]						
			12 bit mode f_{ADCK} > 8 MHz	—	—	1	kΩ	C
			4 MHz < f_{ADCK} > 8 MHz	—	—	2	kΩ	C
			f_{ADCK} < 4 MHz	—	—	5	kΩ	C
			10-bit mode f_{ADCK} > 8MHz	—	—	2	kΩ	C
			4 MHz < f_{ADCK} < 8 MHz	—	—	5	kΩ	C
			f_{ADCK} < 4 MHz	—	—	10	kΩ	C
			8-bit mode f_{ADCK} > 8 MHz	—	—	5	kΩ	C
			f_{ADCK} < 8 MHz	—	—	10	kΩ	C
10	f_{ADCK}	ADC Conversion Clock Freq.						
			High Speed (ADLPC=0, ADHSC=1)	1.0	—	8.0	MHz	D
			High Speed (ADLPC=0, ADHSC=0)	1.0	—	5.0	MHz	D
			Low Power (ADLPC=1, ADHSC=1)	1.0	—	2.5	MHz	D

1 Typical values assume V_{DDAD} = 3.0V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 DC potential difference.

3 External to MCU. Assumes ADLSMP=0.

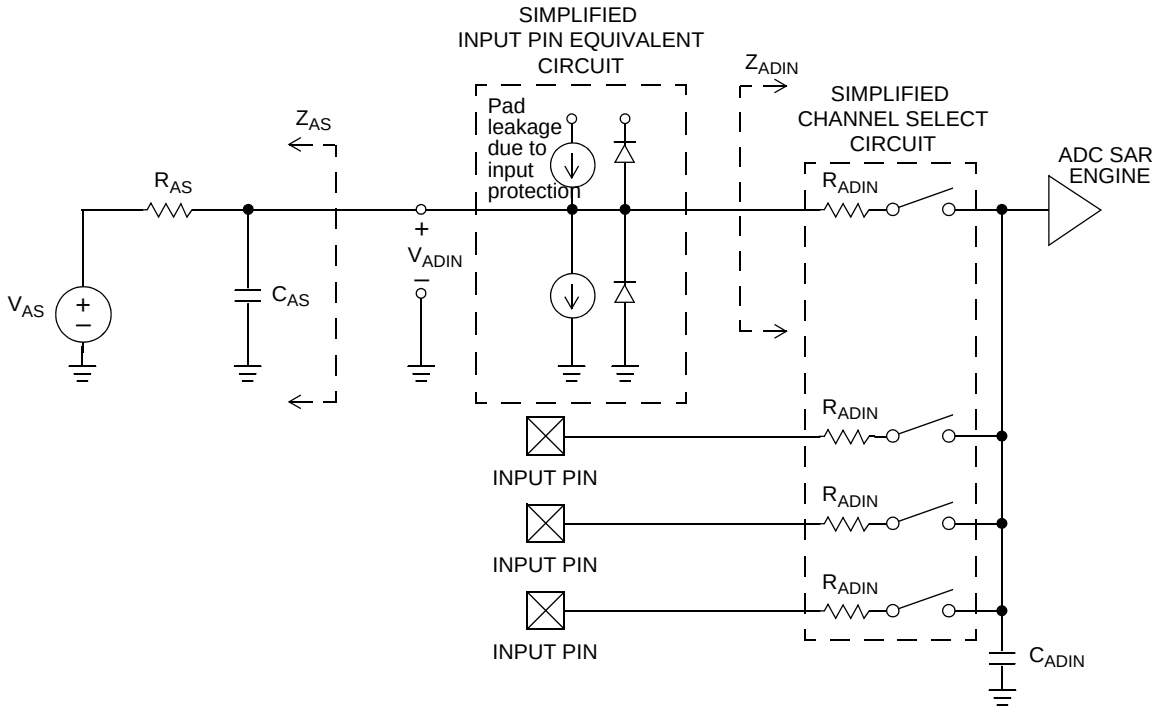


Figure 8. ADC Input Impedance Equivalency Diagram

Table 16. 12-bit SAR ADC Characteristics full operating range ($V_{REFH} = V_{DDAD}$, $V_{REFL} = V_{SSAD}$)

#	Symbol	Characteristic	Conditions[1]	Minimum	Typical[2]	Maximum	Unit	C
1	I_{DDAD}	Supply Current (ADLSMP=0, ADCO=1)	ADLPC=1, ADHSC=0	—	215	—	μA	T
			ADLPC=0, ADHSC=0	—	470	—	μA	T
			ADLPC=0, ADHSC=1	—	610	—	μA	T
			Stop, Reset, Module Off	—	0.01	—	μA	C
2	f_{ADACK}	ADC Asynchronous Clock Source (t_{ADACK} =1/f_{ADACK})	ADLPC=1, ADHSC=0	—	2.4	—	MHz	P
			ADLPC=0, ADHSC=0	—	5.2	—	MHz	P
			ADLPC=0, ADHSC=1	—	6.2	—	MHz	P
3	—	Sample Time — *See Reference Manual for sample times.*						
4	—	Conversion Time — *See Rreference Manual for conversion times.*						
5	TUE	Total Unadjusted Error 32x Hardware Averaging (AVGE = %1 AVGS = %11)	12-bit single-ended mode	—	±1.75	±3.5	LSB[3]	T
			10-bit single-ended mode	—	±0.8	±1.5	LSB[3]	T
			8-bit single-ended mode	—	±0.5	±1.0	LSB[3]	T
6		Differential Non-Linearity	12-bit single-ended mode	—	±0.7	±1	LSB[3]	T
			10-bit single-ended mode	—	±0.5	±0.75	LSB[3]	T
			8-bit single-ended mode	—	±0.2	±0.5	LSB[3]	T

Table 16. 12-bit SAR ADC Characteristics full operating range (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD}) (continued)

#	Symbol	Characteristic	Conditions[1]	Minimum	Typical[2]	Maximum	Unit	C
7	INL	Integral Non-Linearity	12-bit single-ended mode	—	±1.0	±2.5	LSB[3]	T
			10-bit single-ended mode	—	±0.5	±1.0	LSB[3]	T
			8-bit single-ended mode	—	±0.3	±0.5	LSB[3]	T
8	E_{ZS}	Zero-Scale Error (V_{ADIN} = V_{SSAD})	12-bit single-ended mode	—	±0.7	±2.0	LSB[3]	T
			10-bit single-ended mode	—	±0.4	±1.0	LSB[3]	T
			8-bit single-ended mode	—	±0.2	±0.5	LSB[3]	T
9	E_{FS}	Full-Scale Error (V_{ADIN} = V_{DDAD})	12-bit single-ended mode	—	±1.0	±3.5	LSB[3]	T
			10-bit single-ended mode	—	±0.4	±1.5	LSB[3]	T
			8-bit single-ended mode	—	±0.2	±0.5	LSB[3]	T
10	E_Q	Quantization Error	All modes	—	—	±0.5	LSB[3]	D
11	E_{IL}	Input Leakage Error (I_{In} = leakage current (refer to DC Characteristics)	All modes	I_{In} * R_{AS}			mV	D
12	m	Temp Sensor Slope	-40°C to 25°C	—	1.646	—	mV/xC	C
			25°C to 125°C	—	1.769	—	mV/xC	C
13	V_{TEMP25}	Temp Sensor Voltage	25°C	—	701.2	—	mV	C

1 All accuracy numbers assume the ADC is calibrated with V_{REFH}=V_{DDAD}.

2 Typical values assume V_{DDAD} = 3.0V, Temp = 25°C, f_{ADCK}=2.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

3 1 LSB = (V_{REFH} - V_{REFL})/2^N

3.10 MCG and External Oscillator (XOSC) Characteristics

Table 17. MCG (Temperature Range = –40 to 105°C Ambient)

#	Rating		Symbol	Min	Typical	Max	Unit	C
1	Internal reference startup time		t_{irefst}	—	55	100	µs	D
2	Average internal reference frequency	factory trimmed at VDD=3.0V and temp=25°C	f_{int_ft}	—	31.25	—	kHz	C
		user trimmed		31.25	—	39.0625	KHz	C
3	DCO output frequency range - trimmed	Low range (DRS=00)	f_{dco_t}	16	—	20	MHz	C
		Mid range (DRS=01)		32	—	40	MHz	C
		High range[1] (DRS=10)		40	—	60	MHz	C
4	Resolution of trimmed DCO output frequency at fixed voltage and temperature	with FTRIM	$\Delta f_{dco\_res\_t}$	—	± 0.1	± 0.2	$\%f_{dco}$	C
		without FTRIM		—	± 0.2	± 0.4	$\%f_{dco}$	C

3.11 Mini-FlexBus Timing Specifications

A multi-function external bus interface called Mini-FlexBus is provided with basic functionality to interface to slave-only devices up to a maximum bus frequency of 25.1666 MHz. It can be directly connected to asynchronous or synchronous devices such as external boot ROMs, flash memories, gate-array logic, or other simple target (slave) devices with little or no additional circuitry. For asynchronous devices, a simple chip-select based interface can be used.

All processor bus timings are synchronous; that is, input setup/hold and output delay are given in respect to the rising edge of a reference clock, MB_CLK. The MB_CLK frequency is half the internal system bus frequency.

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Mini-FlexBus output clock (MB_CLK). All other timing relationships can be derived from these values.

Table 19. Mini-FlexBus AC Timing Specifications

#	Characteristic	Symbol	Min	Max	Unit	C
1	Frequency of Operation	—	—	25.1666	MHz	—
2	Clock Period	MB1	39.73	—	ns	D
3	Output Valid[1]	MB2	—	20	ns	T
4	Output Hold[1]	MB3	1.0	—	ns	D
5	Input Setup[2]	MB4	22	—	ns	T
6	Input Hold[2]	MB5	10	—	ns	D

1 Specification is valid for all MB_A[19:0], MB_D[7:0], $\overline{\text{MB\_CS}}$[1:0], $\overline{\text{MB\_OE}}$, MB_R/$\overline{\text{W}}$, and MB_ALE.

2 Specification is valid for all MB_D[7:0].

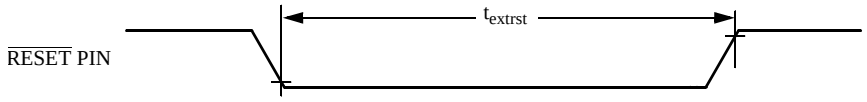


Figure 11. Reset Timing

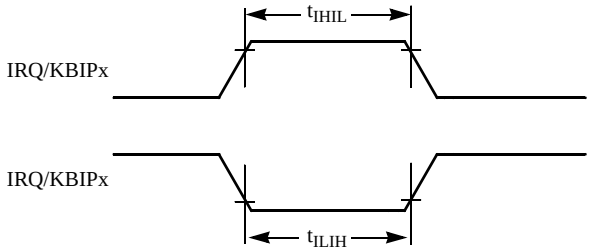
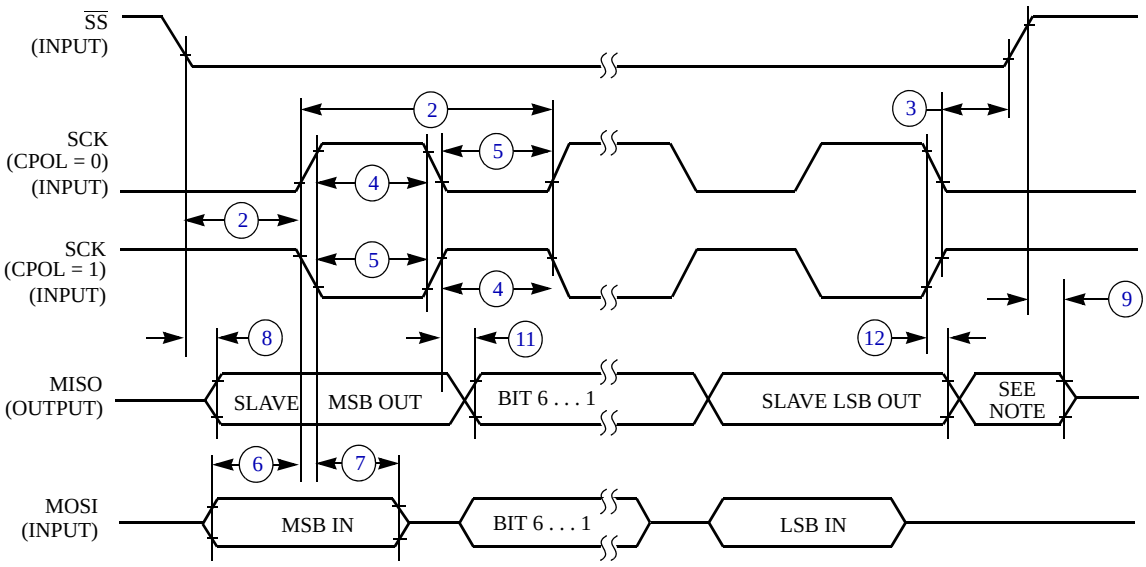


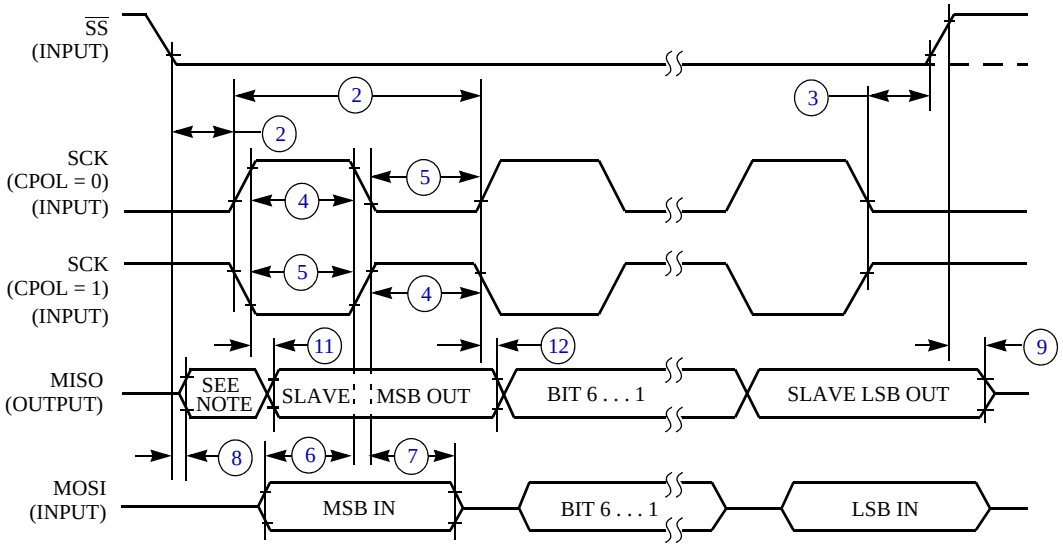
Figure 12. IRQ/KBIPx Timing



NOTE:

1. Not defined, but normally MSB of character just received

Figure 17. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined, but normally LSB of character just received

Figure 18. SPI Slave Timing (CPHA = 1)

Table 24. Internal USB 3.3 V Voltage Regulator Characteristics (continued)

#	Characteristic	Symbol	Minimum	Typical	Maximum	Unit	C
3	V_{USB33} input with internal VREG disabled	$V_{usb33in}$	3	3.3	3.6	V	C
4	VREG Quiescent Current	I_{VRQ}	—	0.5	—	mA	C

3.16 VREF Electrical Specifications

Table 25. VREF Electrical Specifications

#	Characteristic	Symbol	Minimum	Maximum	Unit	C
1	Supply voltage	V_{DDA}	1.80	3.6	V	C
2	Temperature	T_A	–40	105	°C	C
3	Output Load Capacitance	C_L	—	100	nf	D
4	Maximum Load	—	—	10	mA	—
5	Voltage Reference Output with Factory Trim. V_{DD} = 3 V.	Vout	1.148	1.152	V	P
6	Temperature Drift (Vmin - Vmax across the full temperature range)	Tdrift	—	25	mV[1]	T
7	Aging Coefficient[2]	Ac	—	60	μV/year	C
8	Powered down Current (Off Mode, VREFEN = 0, VRSTEN = 0)	I	—	0.10	μA	C
9	Bandgap only (MODE_LV[1:0] = 00)	I	—	75	μA	T
10	Low-Power buffer (MODE_LV[1:0] = 01)	I	—	125	μA	T
11	Tight-Regulation buffer (MODE_LV[1:0] = 10)	I	—	1.1	mA	T
12	Load Regulation (MODE_LV = 10)	—	—	100	μV/mA	C
13	Line Regulation MODE = 1:0, Tight Regulation VDD < 2.3 V, Delta VDDA = 100 mV, VREFH = 1.2 V driven externally with VREFO disabled. (Power Supply Rejection	DC	70	—	dB	C

1 See typical chart below.

2 Linear reliability model (1008 hours stress at 125°C = 10 years operating life) used to calculate Aging μV/year. Vrefo data recorded per month.

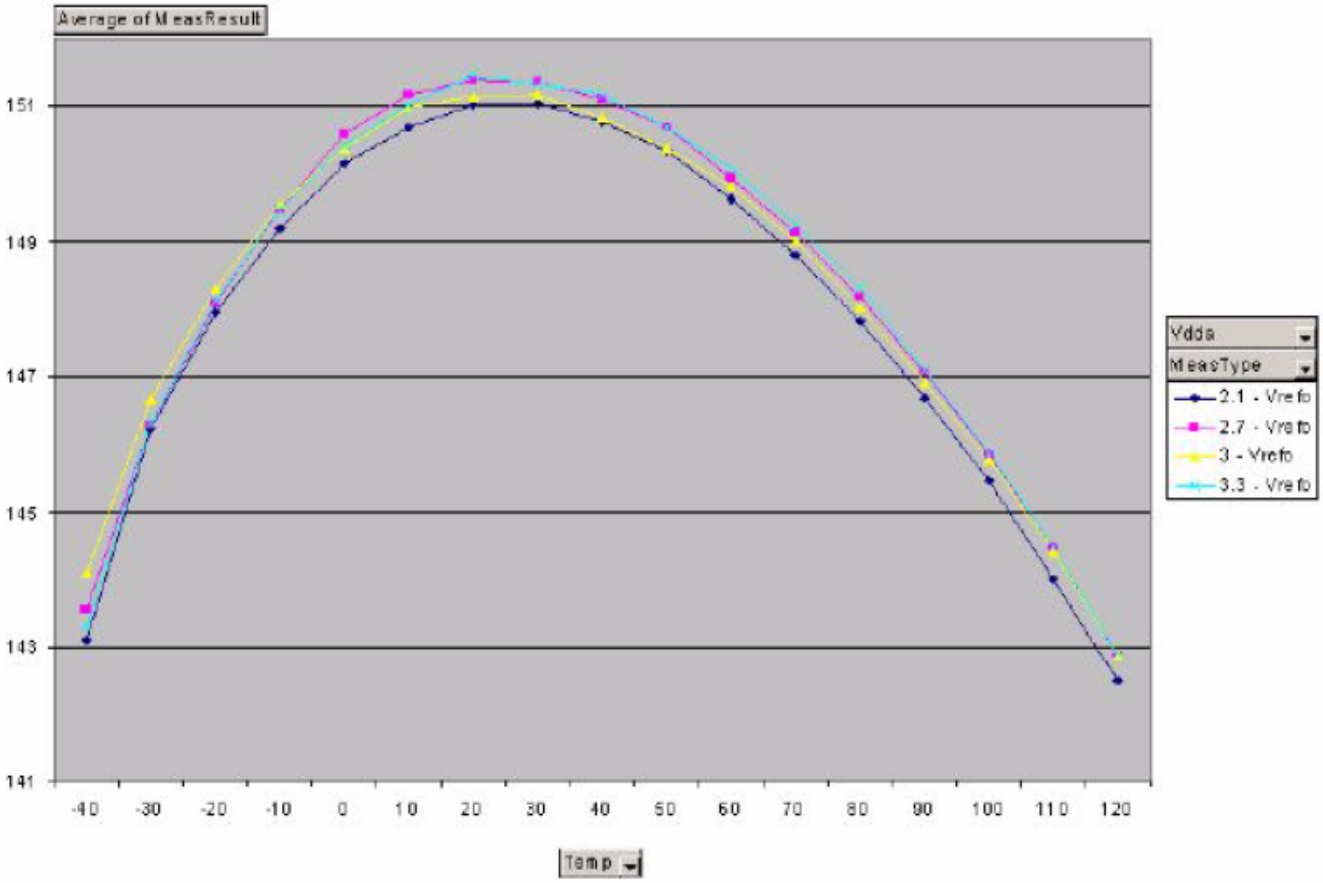


Figure 20. Typical VREF Output vs V_{DD}